



# IMPORTANT NOTICE

10 December 2015

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## 1. Global joint venture starts operations as WeEn Semiconductors

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Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors





# ACT108-600E

AC Thyristor power switch

20 August 2014

Product data sheet

## 1. General description

AC Thyristor power switch in a SOT54 plastic package with self-protective capabilities against low and high energy transients

## 2. Features and benefits

- Exclusive negative gate triggering
- Full cycle AC conduction
- Remote gate separates the gate driver from the effects of the load current
- Very high noise immunity
- Safe clamping of low energy over-voltage transients
- Self-protective turn-on during high energy voltage transients

## 3. Applications

- Fan motor circuits
- Pump motor circuits
- Lower-power highly inductive, resistive and safety loads

## 4. Quick reference data

Table 1. Quick reference data

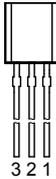
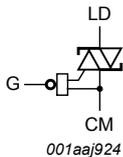
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{\text{DRM}}$	repetitive peak off-state voltage		-	-	600	V
$I_{\text{TSM}}$	non-repetitive peak on-state current	full sine wave; $T_{\text{j}(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; $t_{\text{p}} = 20\text{ ms}$ ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	13	A
$T_{\text{j}}$	junction temperature		-	-	125	$^{\circ}\text{C}$
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{lead}} \leq 71\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a>	-	-	0.8	A
$V_{\text{PP}}$	peak pulse voltage	$T_{\text{j}} = 25\text{ }^{\circ}\text{C}$ ; non-repetitive, off-state; ten pulses on each voltage polarity; 20s or more between successive pulses;; <a href="#">Fig. 4</a>	-	-	2.5	kV
<b>Static characteristics</b>						
$I_{\text{GT}}$	gate trigger current	$V_{\text{D}} = 12\text{ V}$ ; $I_{\text{T}} = 100\text{ mA}$ ; LD+ G-; $T_{\text{j}} = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 6</a>	1	-	10	mA



Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD- G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 6</a>	1	-	10	mA
$V_{CL}$	clamping voltage	$I_{CL} = 0.1\text{ mA}$ ; $t_p = 1\text{ ms}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 12</a>	650	-	-	V
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$ ; $T_j = 125\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit; <a href="#">Fig. 9</a>	2000	-	-	V/ $\mu$ s
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_j = 125\text{ °C}$ ; $I_{T(RMS)} = 0.8\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; (snubberless condition); gate open circuit; <a href="#">Fig. 10</a> ; <a href="#">Fig. 11</a>	0.5	-	-	A/ms

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	CM	common	 <p>TO-92 (SOT54)</p>	 <p>001aaJ924</p>
2	G	gate		
3	LD	load		

## 6. Ordering information

Table 3. Ordering information

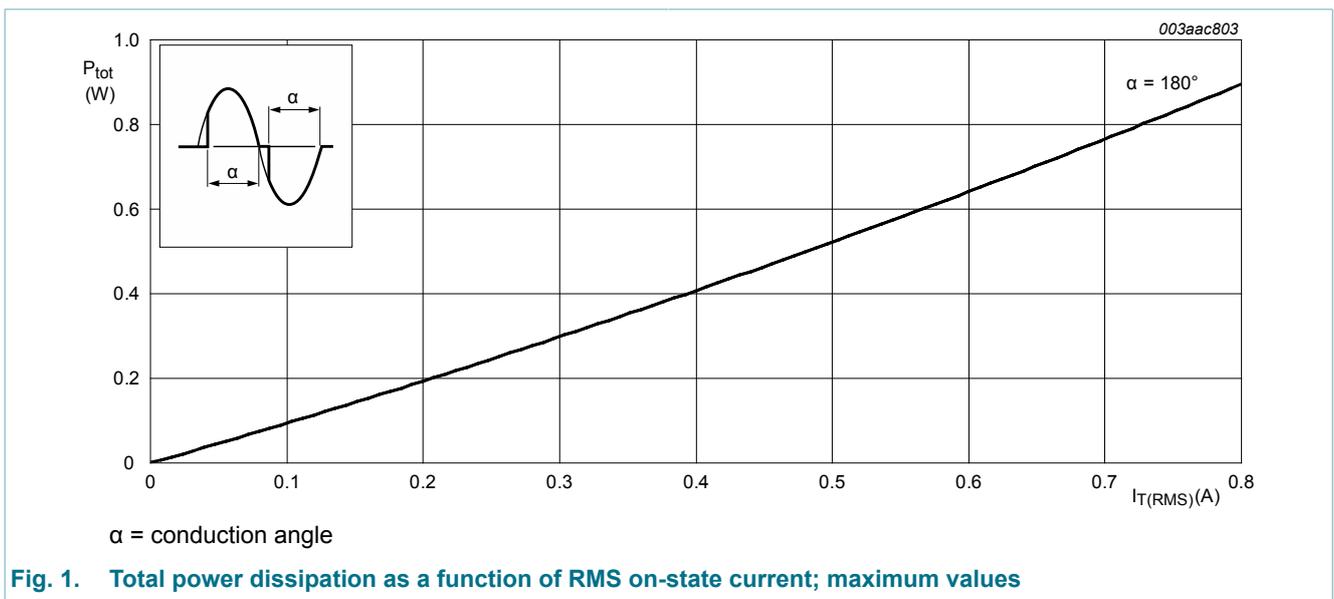
Type number	Package		
	Name	Description	Version
ACT108-600E	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

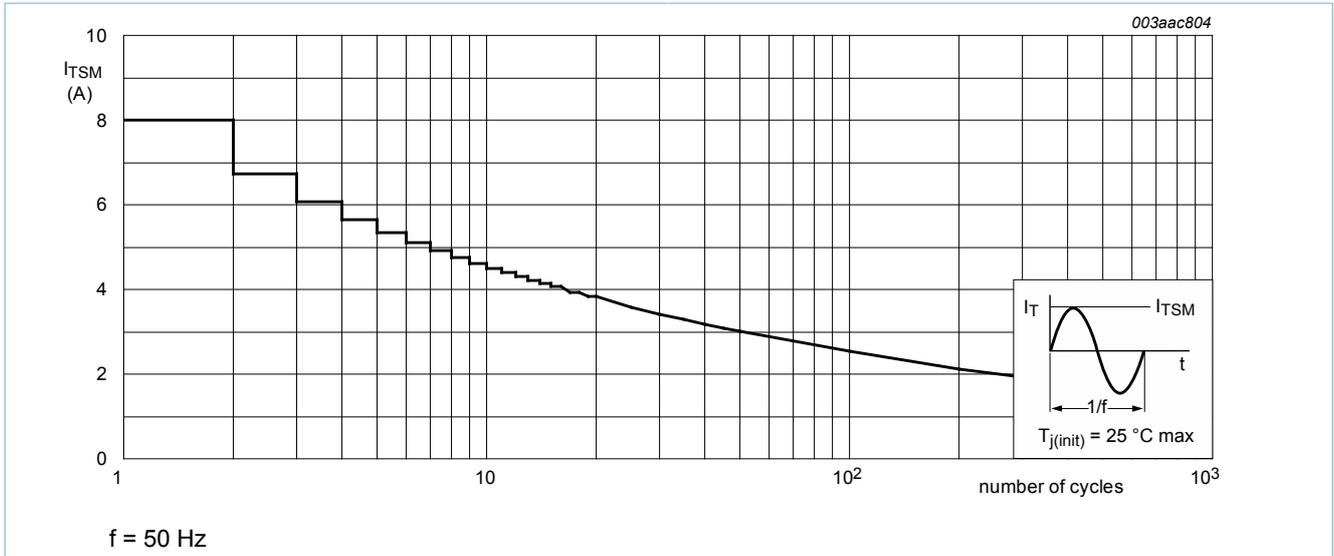
## 7. Limiting values

**Table 4. Limiting values**

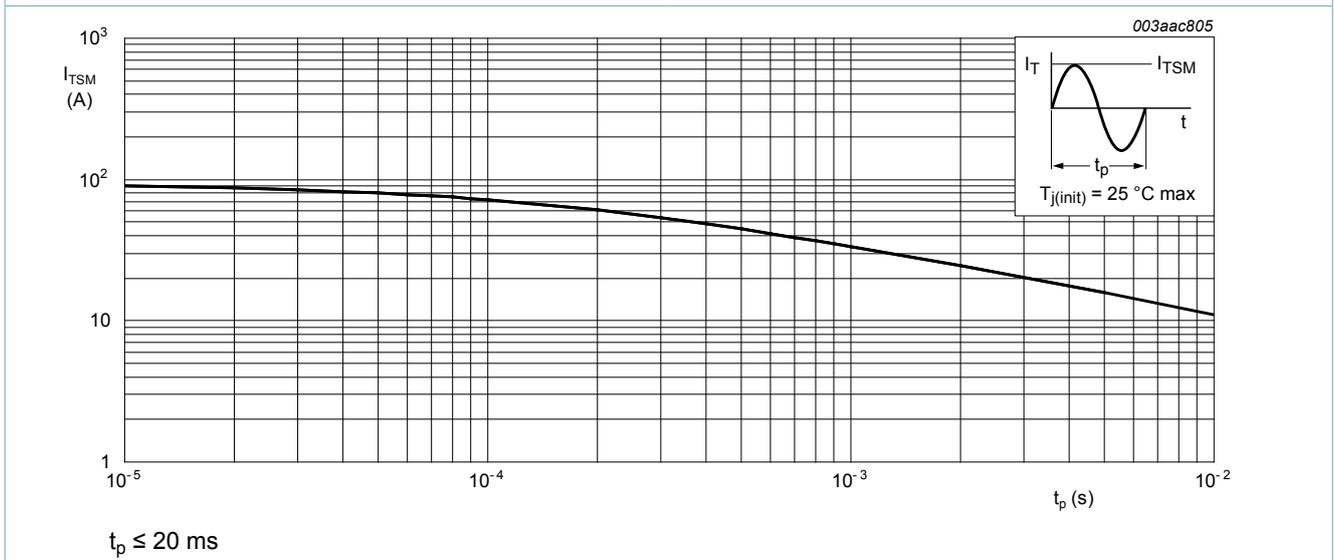
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{lead} \leq 71\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a>	-	0.8	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	13	A
		full sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 16.7\text{ ms}$	-	14.3	A
$I^2t$	$I_2t$ for fusing	$t_p = 10\text{ ms}$ ; SIN	-	0.32	$\text{A}^2\text{s}$
$di_T/dt$	rate of rise of on-state current	$I_T = 1\text{ A}$ ; $I_G = 20\text{ mA}$ ; $di_G/dt = 0.2\text{ A}/\mu\text{s}$	-	100	$\text{A}/\mu\text{s}$
$I_{GM}$	peak gate current	$t = 20\text{ }\mu\text{s}$	-	1	A
$V_{GM}$	peak gate voltage	positive applied gate voltage	-	15	V
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
$T_{stg}$	storage temperature		-40	150	$^{\circ}\text{C}$
$T_j$	junction temperature		-	125	$^{\circ}\text{C}$
$V_{PP}$	peak pulse voltage	$T_j = 25\text{ }^{\circ}\text{C}$ ; non-repetitive, off-state; ten pulses on each voltage polarity; 20s or more between successive pulses;; <a href="#">Fig. 4</a>	-	2.5	kV

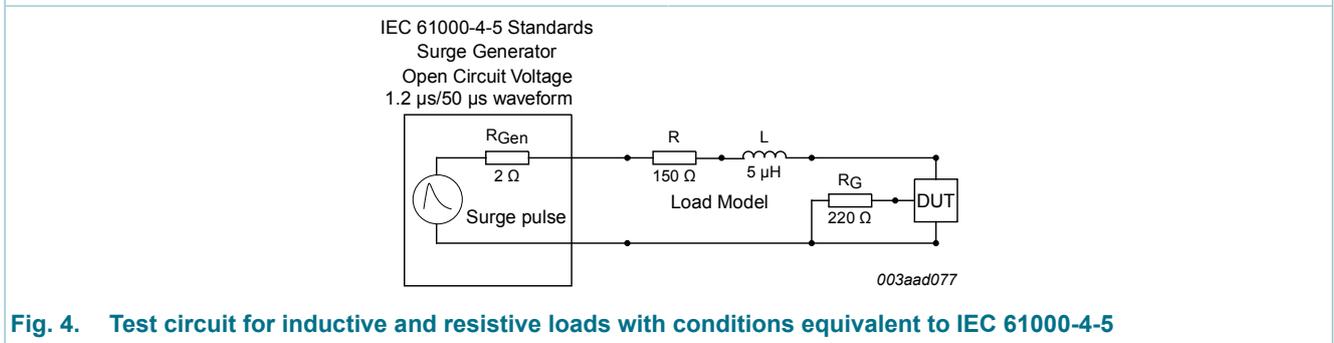




**Fig. 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values**



**Fig. 3. Non-repetitive peak on-state current as a function of pulse width; maximum values**



**Fig. 4. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5**

## 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	full cycle with heatsink compound; <a href="#">Fig. 5</a>	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	full cycle; printed-circuit board mounted; lead length 4 mm	-	150	-	K/W

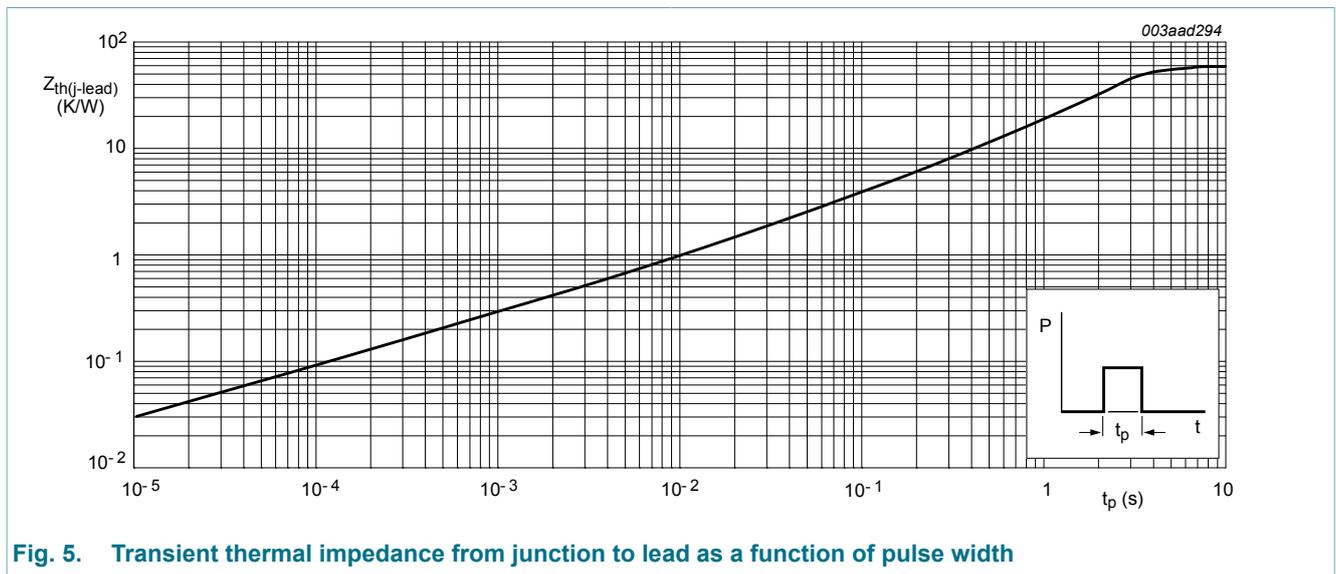
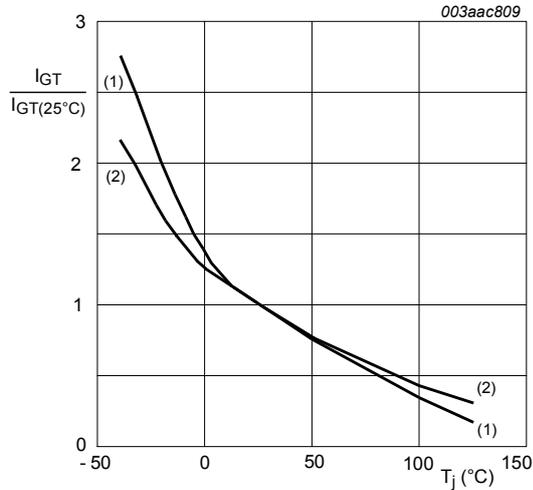


Fig. 5. Transient thermal impedance from junction to lead as a function of pulse width

## 9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD+ G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 6</a>	1	-	10	mA
		$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD- G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 6</a>	1	-	10	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 100\text{ mA}$ ; LD+ G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	-	25	mA
		$V_D = 12\text{ V}$ ; $I_G = 100\text{ mA}$ ; LD- G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	-	20	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	-	20	mA
$V_T$	on-state voltage	$I_T = 1.1\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	-	-	1.3	V
$V_{GT}$	gate trigger voltage	$V_D = 400\text{ V}$ ; $I_T = 100\text{ mA}$ ; $T_j = 125\text{ °C}$	0.15	-	-	V
		$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; $T_j = 25\text{ °C}$	-	-	1	V
$I_D$	off-state current	$V_D = 600\text{ V}$ ; $T_j = 25\text{ °C}$	-	-	2	$\mu\text{A}$
		$V_D = 600\text{ V}$ ; $T_j = 125\text{ °C}$	-	-	0.2	mA
$V_{CL}$	clamping voltage	$I_{CL} = 0.1\text{ mA}$ ; $t_p = 1\text{ ms}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 12</a>	650	-	-	V
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$ ; $T_j = 125\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit; <a href="#">Fig. 9</a>	2000	-	-	V/ $\mu\text{s}$
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_j = 125\text{ °C}$ ; $I_{T(RMS)} = 0.8\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; (snubberless condition); gate open circuit; <a href="#">Fig. 10</a> ; <a href="#">Fig. 11</a>	0.5	-	-	A/ms



(1) LD+ G-  
(2) LD- G-

Fig. 6. Normalized gate trigger current as a function of junction temperature

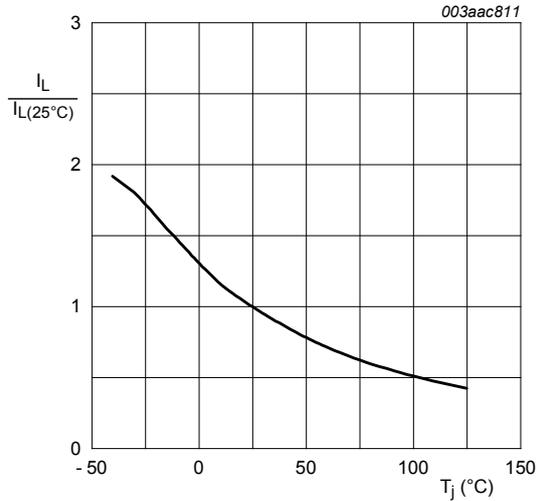
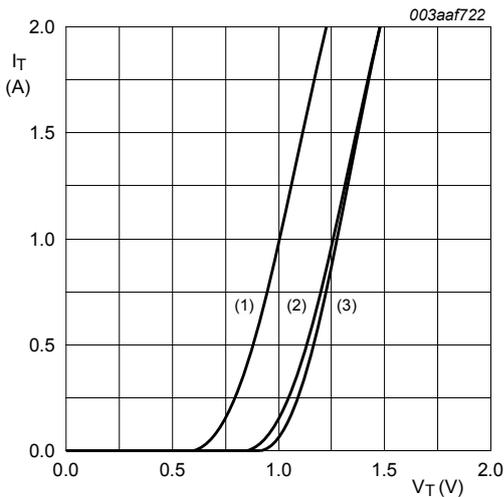


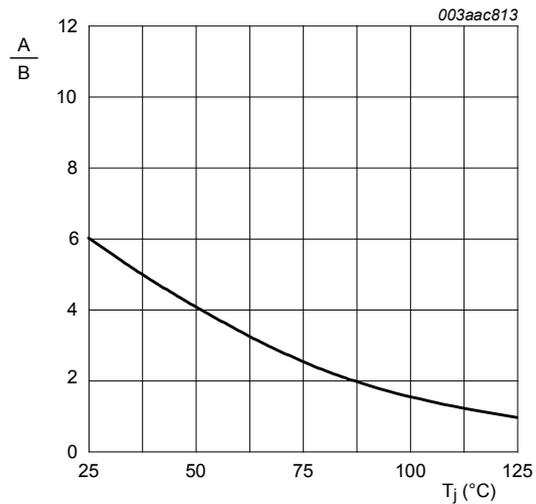
Fig. 7. Normalized latching current as a function of junction temperature



$V_o = 0.758 \text{ V}; R_s = 0.263 \text{ } \Omega$

(1)  $T_j = 125 \text{ } ^\circ\text{C}$ ; typical values  
(2)  $T_j = 125 \text{ } ^\circ\text{C}$ ; maximum values  
(3)  $T_j = 25 \text{ } ^\circ\text{C}$ ; maximum values

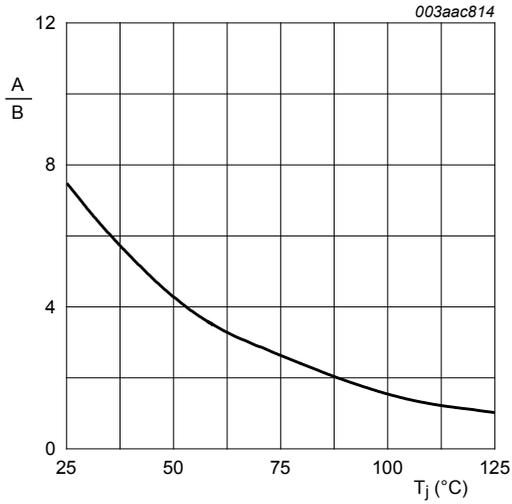
Fig. 8. On-state current as a function of on-state voltage



$A = dV_D/dt$  at condition  $T_j \text{ } ^\circ\text{C}$

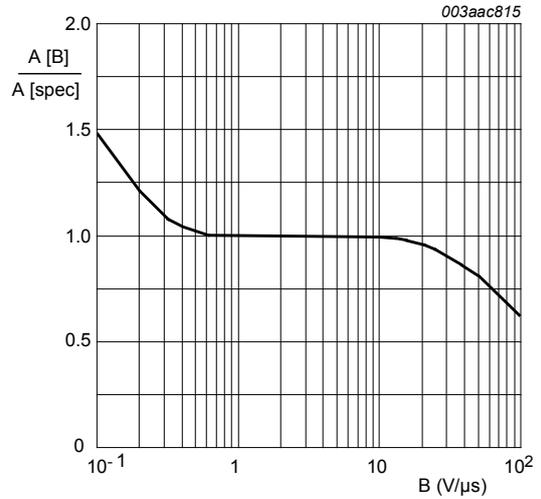
$B = dV_D/dt$  at condition  $T_j [125] \text{ } ^\circ\text{C}$

Fig. 9. Normalized rate of rise of off-state voltage as a function of junction temperature



$A = di_{com}/dt$  at condition  $T_j$  °C  
 $B = di_{com}/dt$  at condition  $T_j$  [125] °C  
 $V_D = 400$  V

Fig. 10. Normalized critical rate of rise of commutating current as a function of junction temperature



$A [B] = di_{com}/dt$  at condition B,  $dV_{com}/dt$   
 $A [spec]$  is the data sheet value for  $di_{com}/dt$   
 turn-off time is less than 20 ms

Fig. 11. Normalized critical rate of change of commutating current as a function of critical rate of change of commutating voltage; minimum values

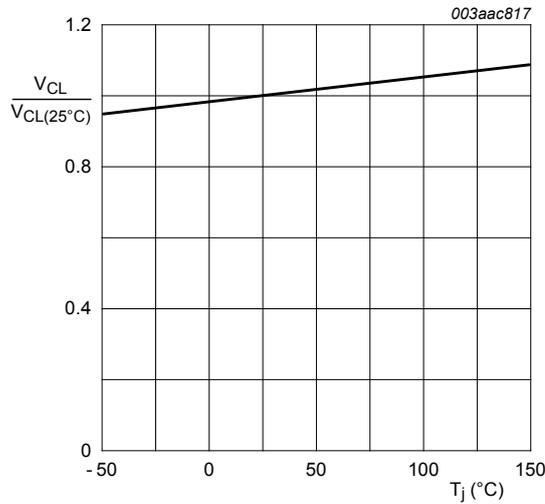
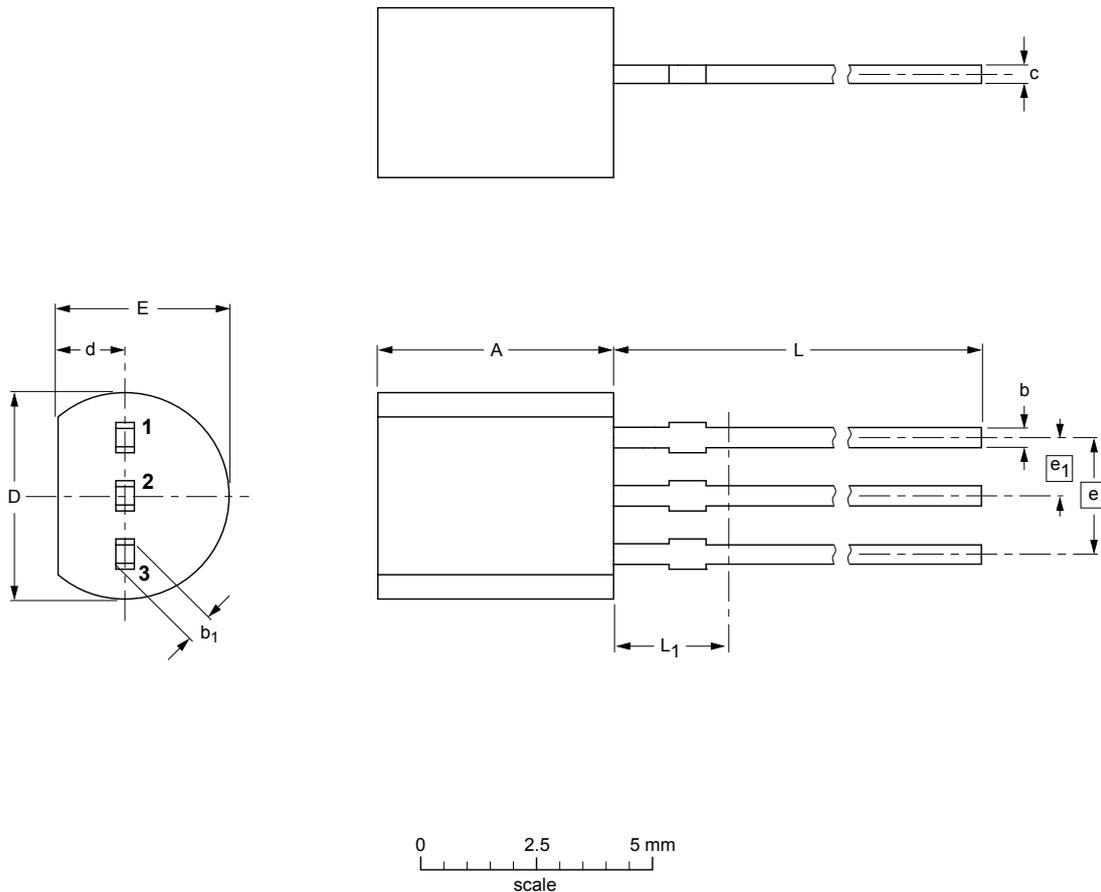


Fig. 12. Normalized clamping voltage (upper limit) as a function of junction temperature; minimum values

### 10. Package outline

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



**DIMENSIONS** (mm are the original dimensions)

UNIT	A	b	b <sub>1</sub>	c	D	d	E	e	e <sub>1</sub>	L	L <sub>1</sub> <sup>(1)</sup> max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

**Note**

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT54		TO-92	SC-43A			-04-06-28- 04-11-16

Fig. 13. Package outline TO-92 (SOT54)

## 11. Legal information

### 11.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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